

General Description:

HM25N65A the silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-3P, which accords with the RoHS standard..

Features:

- **Fast Switching**
- **Low ON Resistance**($R_{DS(on)} \leq 0.5\Omega$)
- **Low Gate Charge** (Typical Data: 65nC)
- **Low Reverse transfer capacitances**(Typical: 20pF)
- **100% Single Pulse avalanche energy Test**

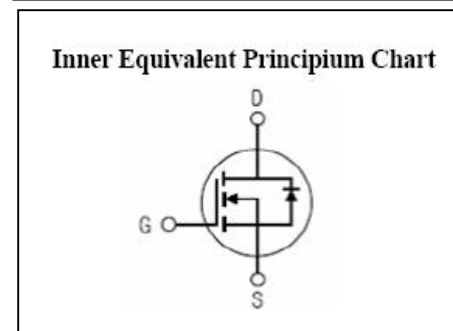
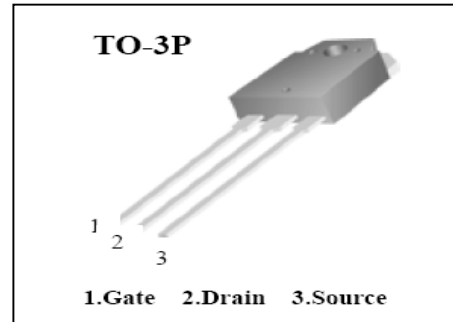
Applications:

Power switch circuit of adaptor and charger.

Absolute (T_c = 25 °C unless otherwise specified):

Symbol	Parameter	Rating	Units
V _{DSS}	Drain-to-Source Voltage	650	V
I _D	Continuous Drain Current	25	A
	Continuous Drain Current T _C = 100 °C	13.5	A
I _{DM} ^{a1}	Pulsed Drain Current	75	A
V _{GS}	Gate-to-Source Voltage	±30	V
E _{AS} ^{a2}	Single Pulse Avalanche Energy	550	mJ
E _{AR} ^{a1}	Avalanche Energy ,Repetitive	50	mJ
I _{AR} ^{a1}	Avalanche Current	3.2	A
dv/dt ^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P _D	Power Dissipation	85	W
	Derating Factor above 25°C	0.68	W/°C
T _J , T _{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	°C
T _L	Maximum Temperature for Soldering	300	°C

V _{DSS}	650	V
I _D	25	A
P _D (T _C =25 °C)	85	W
R _{DS(ON)Typ}	0.25	Ω



Electrical Characteristics (Tc= 25°C unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	650	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$ID=250\mu A, \text{Reference } 25^\circ C$	--	0.5	--	V/°C
I_{DSS}	Drain to Source Leakage Current	$V_{DS} = 650V, V_{GS}= 0V, T_a = 25^\circ C$	--	--	1	μA
		$V_{DS} = 520V, V_{GS}= 0V, T_a = 125^\circ C$			100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}= 30V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS} = -30V$	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=10A$	--	0.25	0.3	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	--	4.0	V
Pulse width $tp \leq 300\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Trans conductance	$V_{DS}=15V, I_D =10A$	--	17	--	S
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1.0MHz$	--	2400		pF
C_{oss}	Output Capacitance		--	225		
C_{rss}	Reverse Transfer Capacitance		--	20		

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D = 25A, V_{DD} = 325V$ $R_G = 25\Omega$	--	35		ns
t_r	Rise Time		--	82		
$t_{d(OFF)}$	Turn-Off Delay Time		--	180		
t_f	Fall Time		--	90		
Q_g	Total Gate Charge	$I_D = 25A, V_{DD} = 325V$ $V_{GS} = 10V$	--	65		nC
Q_{gs}	Gate to Source Charge		--	11	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	26	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	25	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	75	A
V_{SD}	Diode Forward Voltage	$I_S=25A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=25A, T_J = 25^{\circ}C$	--	390	--	ns
Q_{rr}	Reverse Recovery Charge	$dI_F/dt=100A/us, V_{GS}=0V$	--	3.4	--	μC
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	1.47	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-Ambient	100	$^{\circ}C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=10mH, I_D=10.5A$, Start $T_J=25^{\circ}C$

^{a3}: $I_{SD}=25A, di/dt \leq 200A/us, V_{DD} \leq BV_{DSS}$, Start $T_J=25^{\circ}C$

Characteristics Curve:

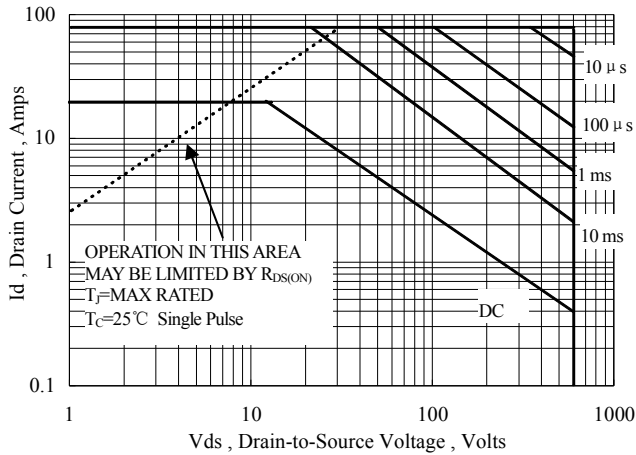


Figure 1 Maximum Forward Bias Safe Operating Area

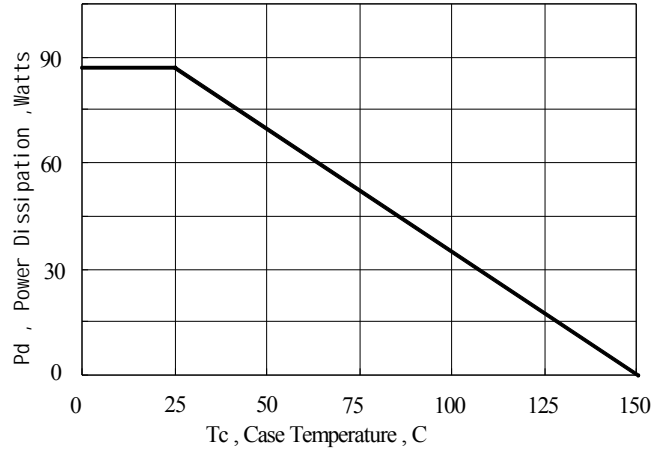


Figure 2 Maximum Power Dissipation vs Case Temperature

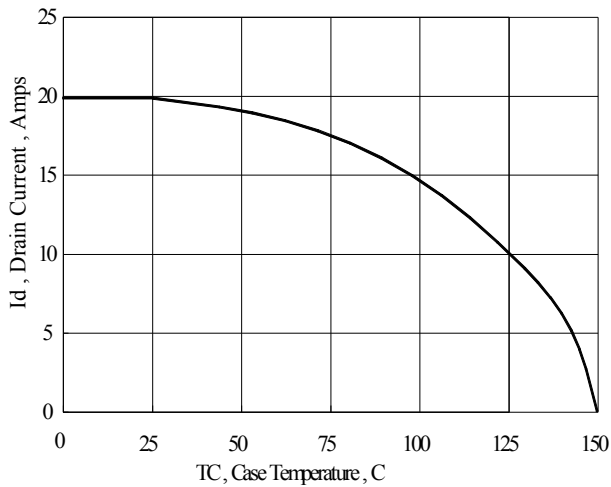


Figure 3 Maximum Continuous Drain Current vs Case Temperature

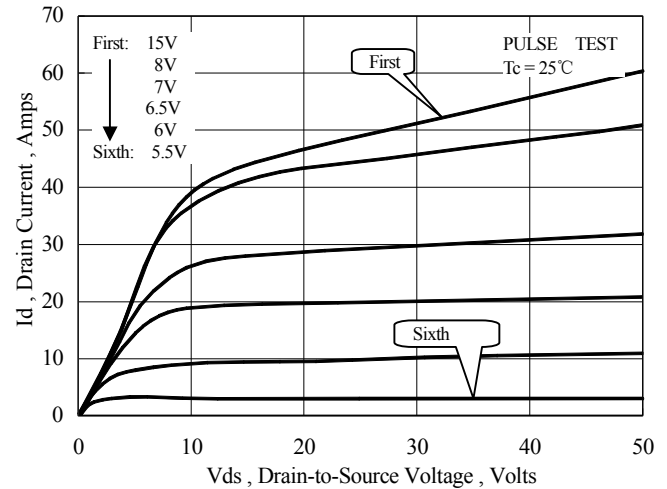


Figure 4 Typical Output Characteristics

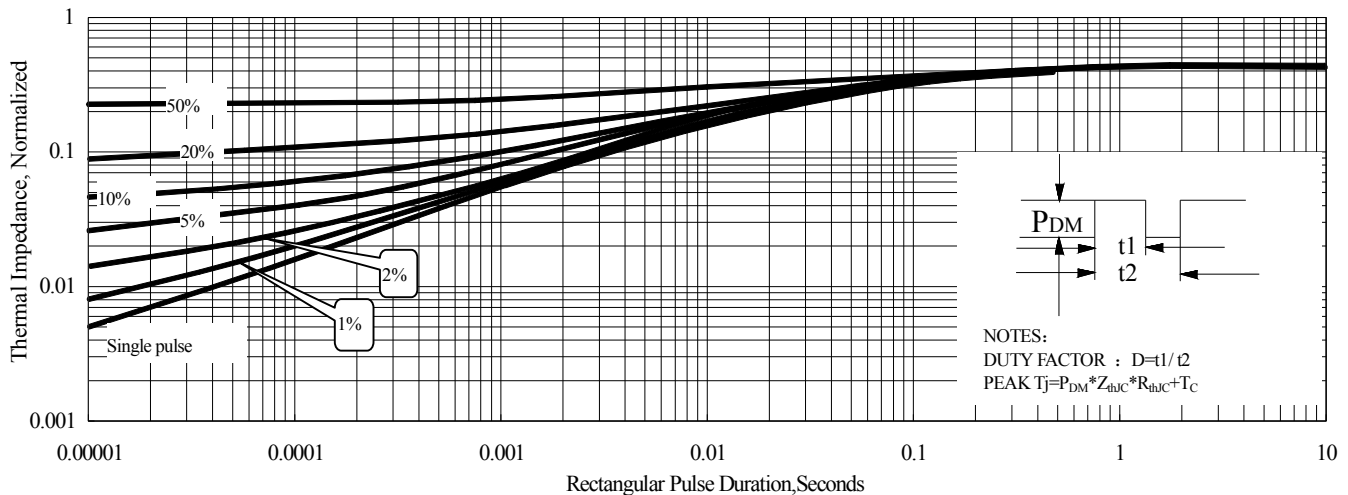


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

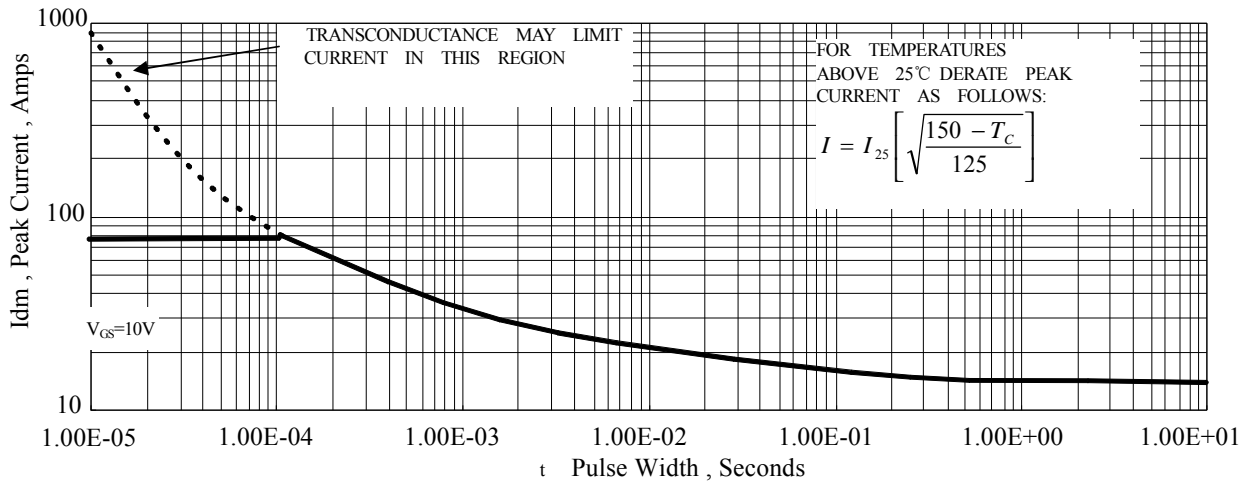


Figure 6 Maximum Peak Current Capability

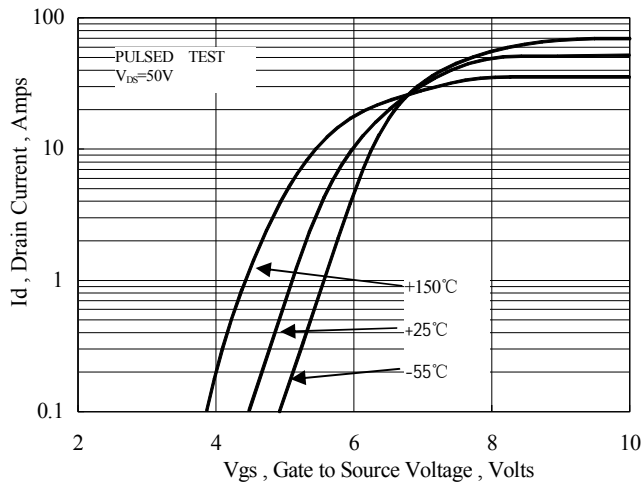


Figure 7 Typical Transfer Characteristics

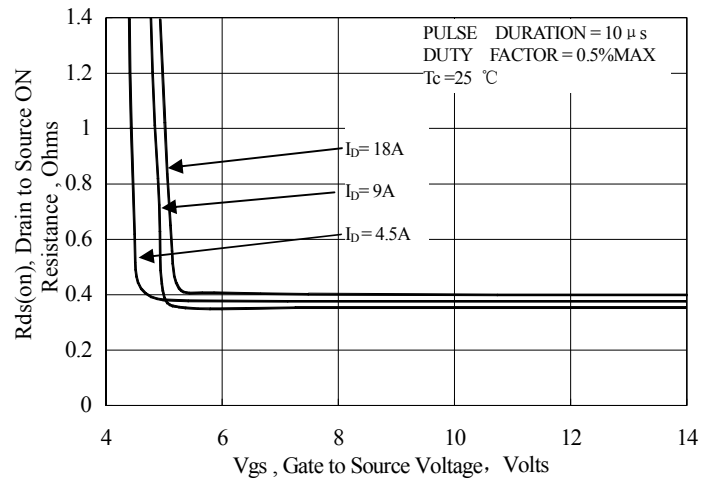


Figure 8 Typical Drain to Source ON Resistance vs. Gate Voltage and Drain Current

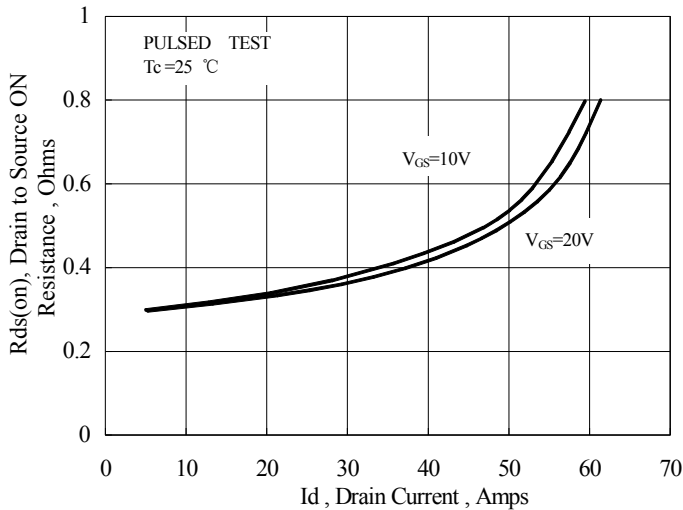


Figure 9 Typical Drain to Source ON Resistance vs. Drain Current

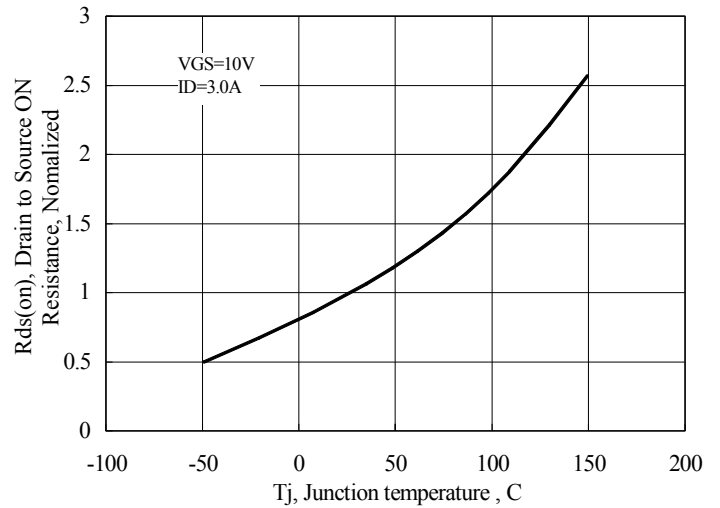


Figure 10 Typical Drain to Source ON Resistance vs. Junction Temperature

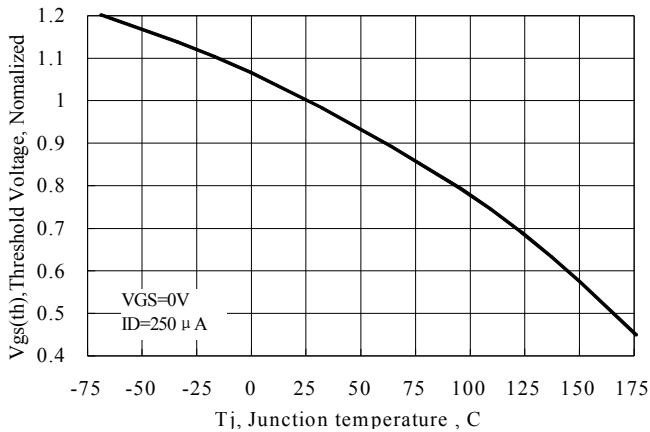


Figure 11 Typical Theshold Voltage vs Junction Temperature

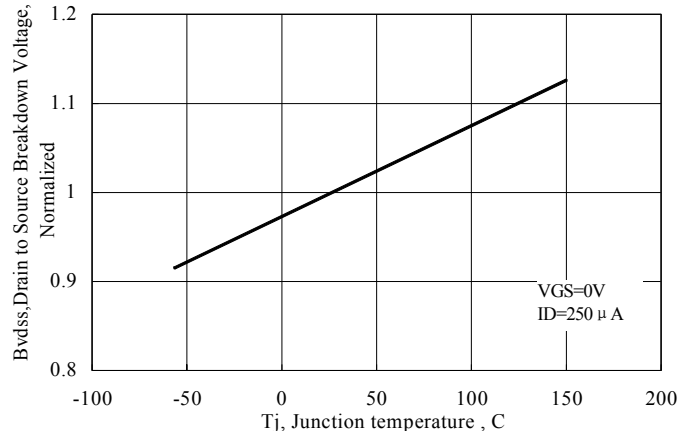


Figure 12 Typical Breakdown Voltage vs Junction Temperature

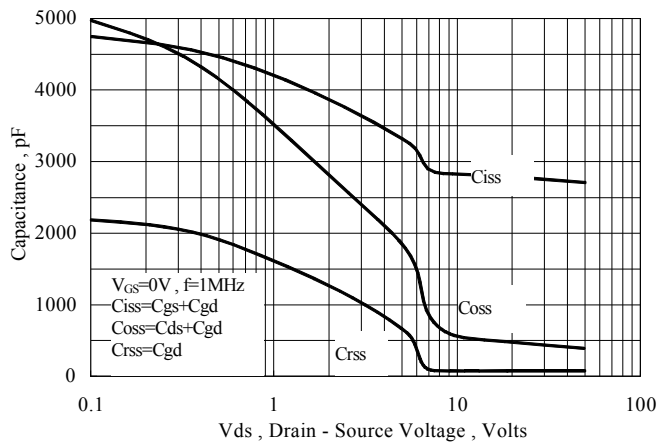


Figure 13 Typical Capacitance vs Drain to Source Voltage

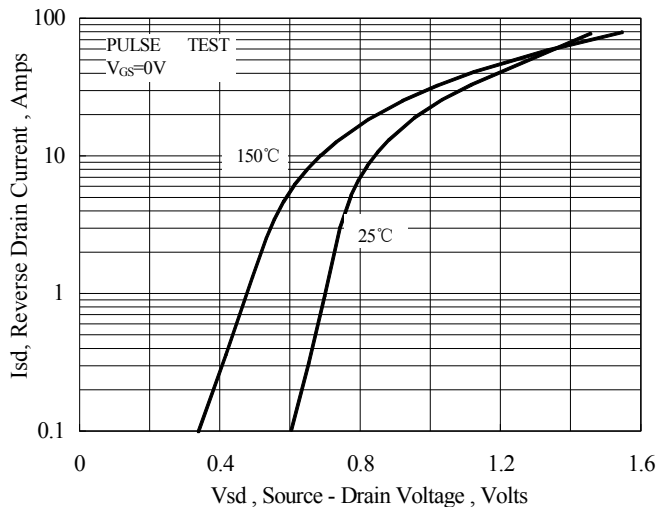
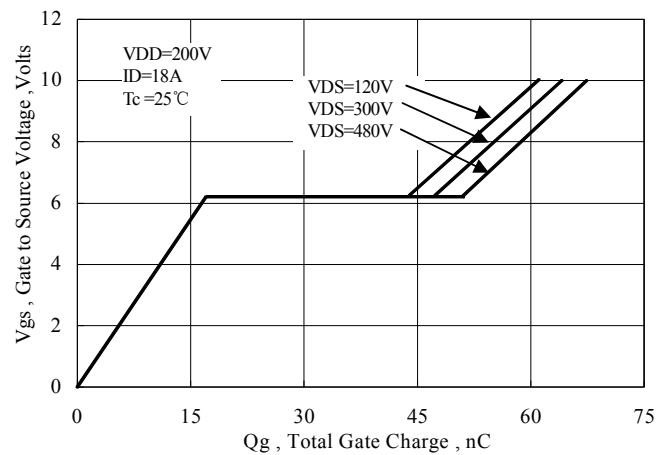


Figure 15 Typical Body Diode Transfer Characteristics

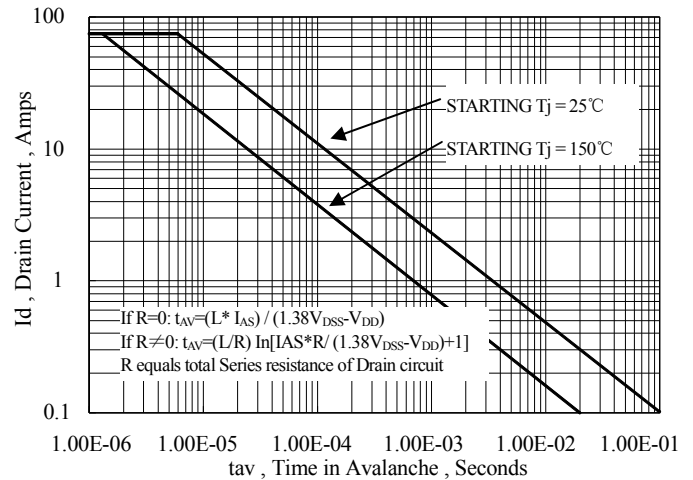


Figure 16 Unclamped Inductive Switching Capability

Test Circuit and Waveform

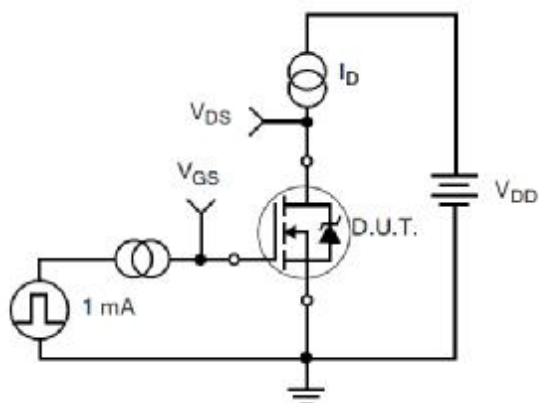


Figure 17. Gate Charge Test Circuit

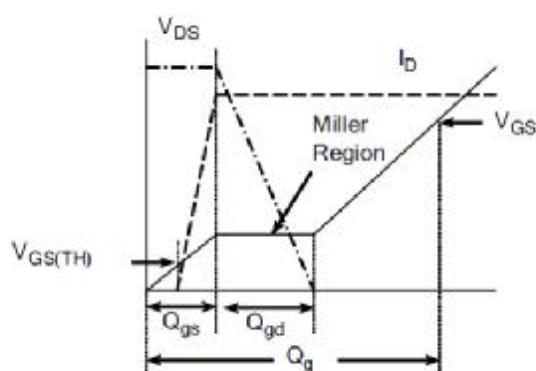


Figure 18. Gate Charge Waveform

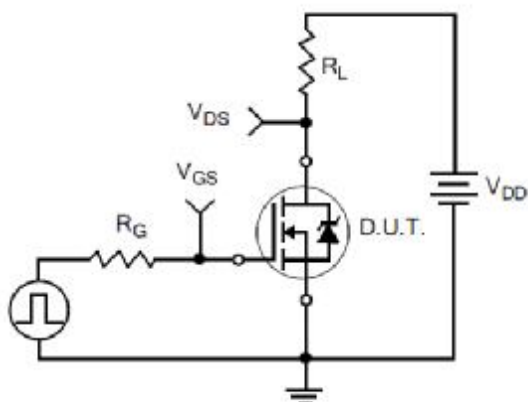


Figure 19. Resistive Switching Test Circuit

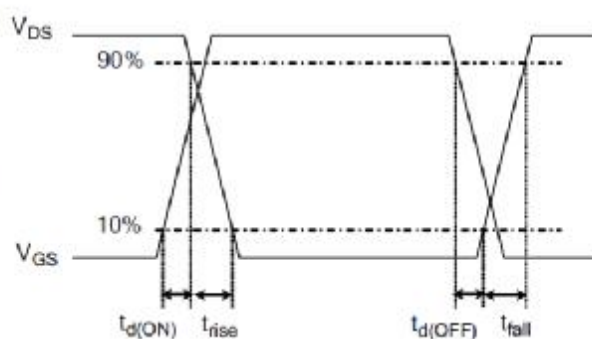


Figure 20. Resistive Switching Waveforms

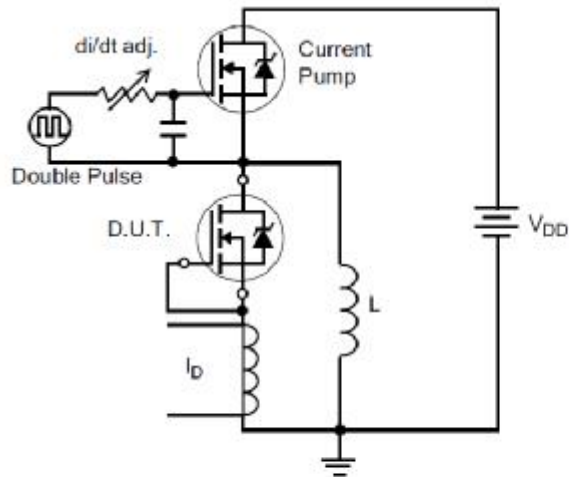


Figure 21. Diode Reverse Recovery Test Circuit

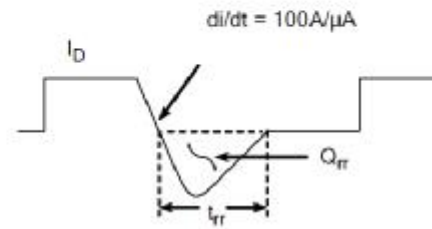


Figure 22. Diode Reverse Recovery Waveform

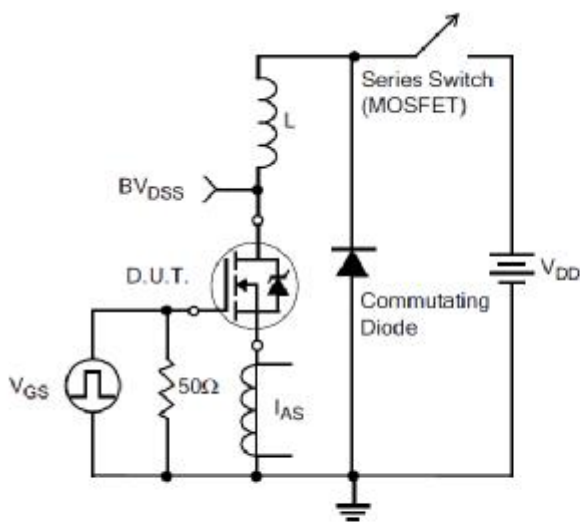


Figure 23. Unclamped Inductive Switching Test Circuit

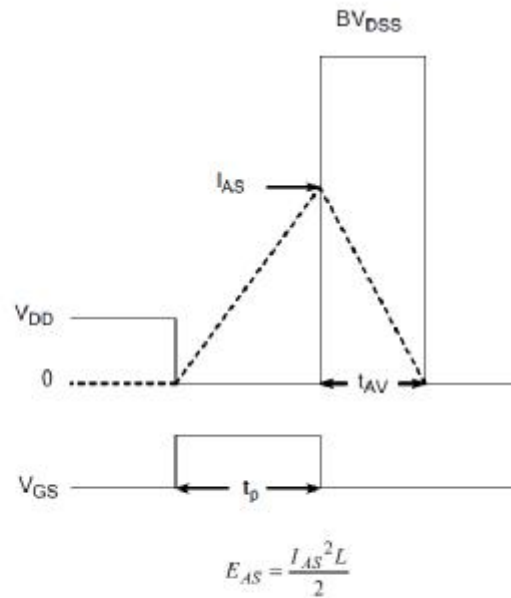
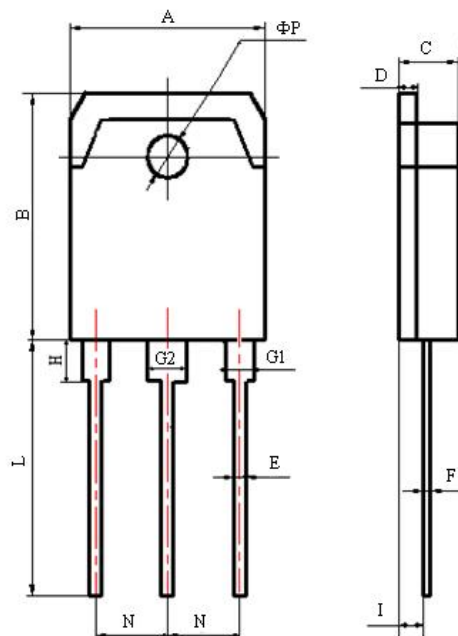


Figure 24. Unclamped Inductive Switching Waveforms

Package Information:



Items	Values(mm)	
	MIN	MAX
A	15.10	15.90
B	19.30	20.50
C	4.70	4.90
D	1.40	1.60
E	0.90	1.10
F	0.50	0.70
G1	2.00	2.20
G2	3.00	3.20
H	3.00	3.60
I	1.20	1.60
L	19.00	21.00
N	5.25	5.65
Φ P	3.10	3.30

TO-3P(N) Package

The name and content of poisonous and harmful material in products

Part's Name	Hazardous Substance					
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE
Limit	≤0.1%	≤0.1%	≤0.01%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○
Molding Compound	○	○	○	○	○	○
Chip	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○
Solder	×	○	○	○	○	○
Note	○: means the hazardous material is under the criterion of SJ/T11363-2006. ×: means the hazardous material exceeds the criterion of SJ/T11363-2006. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.					

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heatsink, please pay attention to the torsional moment and the smoothness of the heatsink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by H&M Semiconductor and subject to regular change without notice.